## Vibrational properties of CdGa<sub>2</sub>S<sub>4</sub> at high pressure

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## **ABSTRACT**

Raman scattering measurements have been performed in cadmium digallium sulphide (CdGa<sub>2</sub>S<sub>4</sub>) with defect chalcopyrite structure up to 25 GPa in order to study its pressure-induced phase transitions. These measurements have been complemented and compared with lattice-dynamics *ab initio* calculations including the TO-LO splitting at high pressures in order to provide a better assignment of experimental Raman modes. In addition, experimental and theoretical Grüneisen parameters have been reported in order to calculate the molar heat capacity and thermal expansion coefficient of CdGa<sub>2</sub>S<sub>4</sub>. Our measurements provide evidence that CdGa<sub>2</sub>S<sub>4</sub> undergoes an irreversible phase transition above 15 GPa to a Raman-inactive phase, likely with a disordered rock salt structure. Moreover, the Raman spectrum observed on downstroke from 25 GPa to 2 GPa has been attributed to a new phase, tentatively identified as a disordered zinc blende structure, that undergoes a reversible phase transition to the Raman-inactive phase above 10 GPa.

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## I. INTRODUCTION

 $A^{\rm II}B_2^{\rm III}X_4^{\rm VI}$  compounds are distorted tetrahedrally-coordinated compounds characterized by the presence of stoichiometric vacancies in the unit cell. Vacancies are needed to obey the Grimm-Sommerfeld rule and maintain the charge neutrality, as in other tetrahedrally-coordinated structures derived from the diamond structure.  $A^{\rm II}B_2^{\rm III}X_4^{\rm VI}$  compounds are also known as ordered-vacancy compounds (OVCs) and they represent a clear intermediate stage between perfect crystals and amorphous materials. In particular, CdGa<sub>2</sub>S<sub>4</sub> crystallizes in the defect chalcopyrite (DC) structure [space group (s.g.)  $I\bar{4}$ , No. 82, Z=2]. Its unit cell can be visualized by doubling the zinc blende (ZB) one (s.g.  $F\bar{4}3m$ , No. 216, Z=4) of an AX compound along the c-axis and replacing four equal cations of the ZB structure by one Cd cation, two Ga cations, and one vacancy [Fig. 1(a)].

The presence of vacancies in OVCs yields relevant properties in comparison with their homologue AX, BX, and  $ABX_2$  compounds, like higher compressibilities,  $^{2-4}$  good performance as host materials and suitable valence electron concentration, large second harmonic generation, and extensive damage threshold for mid-IR nonlinear optics. The most remarkable fields of application of OVCs, due to their wide bandgap, high photosensitivity, bright photoluminescence, and long-term stability of many parameters are photovoltaic cells, optoelectronic devices, temperature sensors, and optical filters. In particular, CdGa<sub>2</sub>S<sub>4</sub> has raised considerable attention in the field of nonlinear optics.

Several high-pressure (HP) studies of the properties of OVCs have been reported in the last few years. A combination of multiple experimental techniques such as X-ray diffraction (XRD), Raman

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